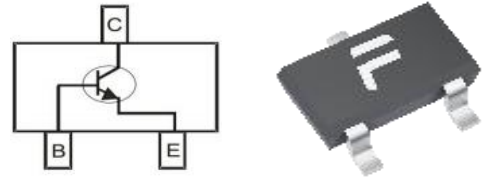


SOT-323 Bipolar Transistor 双极型三极管

■ Features 特点

NPN Switching 开关



■ Absolute Maximum Ratings 最大额定值

Characteristic 特性参数	Symbol 符号	Rat 额定值	Unit 单位
Collector-Base Voltage 集电极基极电压	V_{CB0}	60	V
Collector-Emitter Voltage 集电极发射极电压	V_{CEO}	40	V
Emitter-Base Voltage 发射极基极电压	V_{EBO}	6	V
Collector Current 集电极电流	I_C	600	mA
Power dissipation 耗散功率	$P_C(T_a=25^\circ\text{C})$	200	mW
Thermal Resistance Junction-Ambient 热阻	$R_{\theta JA}$	625	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature 结温和储藏温度	T_J, T_{stg}	-55to+150 $^\circ\text{C}$	

■ Device Marking 产品打标

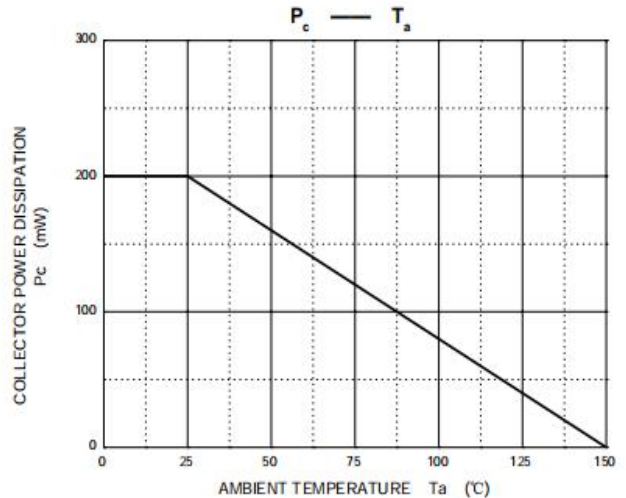
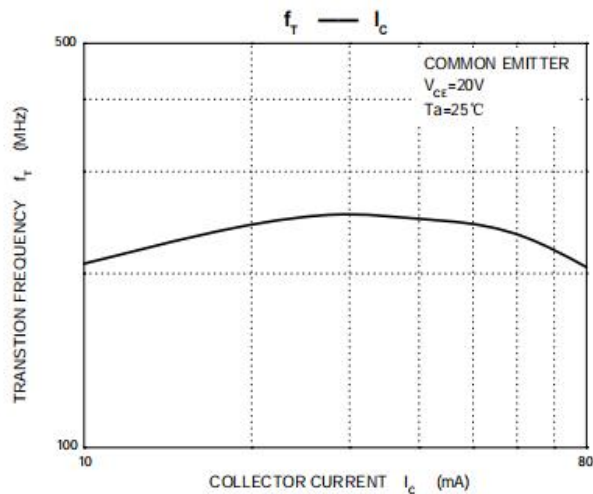
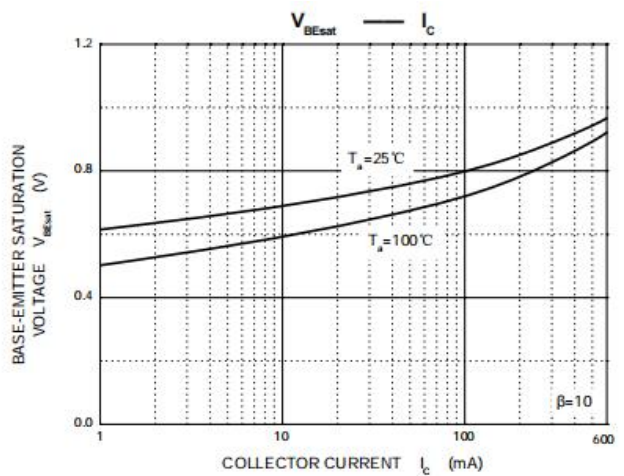
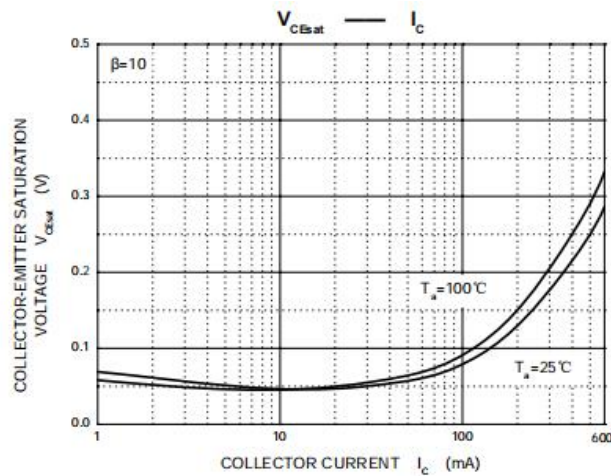
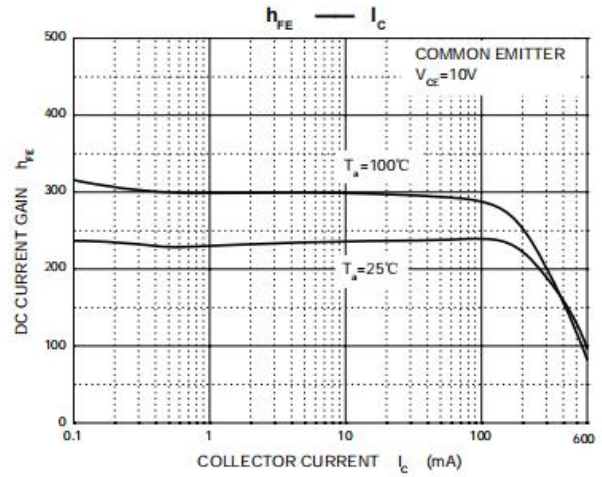
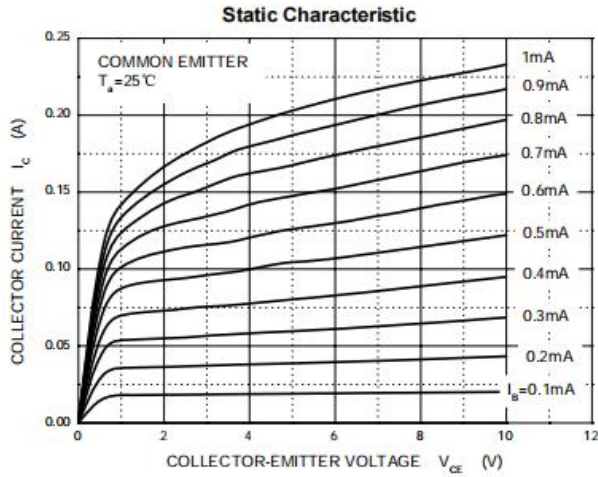
MMBT4401W=2X

■Electrical Characteristics 电特性

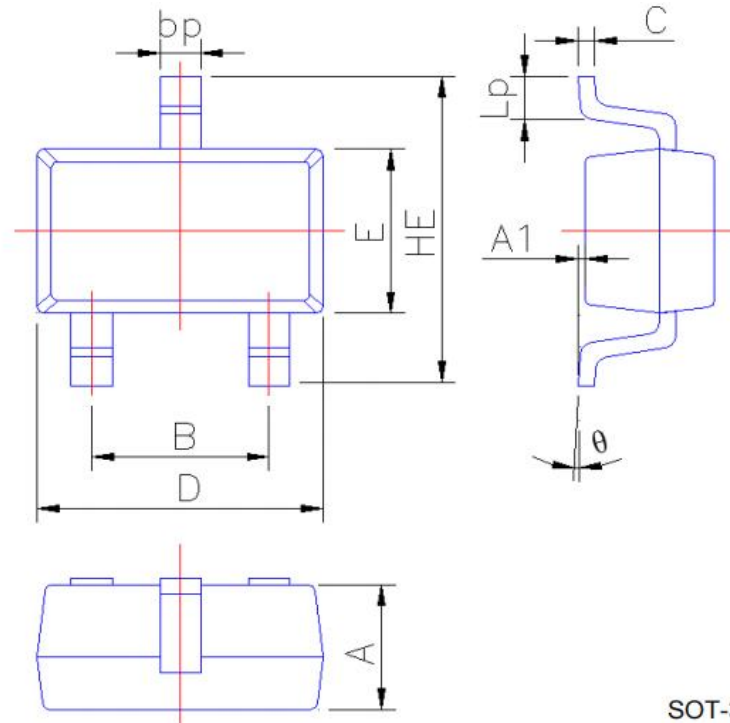
(TA=25°C unless otherwise noted 如无特殊说明, 温度为 25°C)

Characteristic 特性参数	Symbol 符号	Min 最小值	Type 典型值	Max 最大值	Unit 单位
Collector-Base Breakdown Voltage 集电极基极击穿电压(I _C = 0.1mA, I _E =0)	BV _{CBO}	60	—	—	V
Collector-Emitter Breakdown Voltage 集电极发射极击穿电压(I _C = 1mA, I _B =0)	BV _{CEO}	40	—	—	V
Emitter-Base Breakdown Voltage 发射极基极击穿电压(I _E = 0.1mA, I _C =0)	BV _{EBO}	6	—	—	V
Collector-Base Leakage Current 集电极基极漏电流(V _{CB} = 35V, I _E =0)	I _{CBO}	—	—	100	nA
Collector-Emitter Leakage Current 集电极发射极漏电流(V _{CE} = 30V, V _{BE} = -0.5V)	I _{CEX}	—	—	100	nA
Emitter-Base Leakage Current 发射极基极漏电流(V _{EB} = 4V, I _C =0)	I _{EBO}	—	—	100	nA
DC Current Gain(V _{CE} = 1V, I _C = 0.1mA) 直流电流增益(V _{CE} = 1V, I _C = 150mA) (V _{CE} = 2V, I _C = 500mA)	H _{FE}	20 100 40	—	300	
Collector-Emitter Saturation Voltage 集电极发射极饱和压降(I _C = 500mA, I _B = 50mA) (I _C = 150mA, I _B = 15mA)	V _{CE(sat)}	—	—	0.75 0.4	V
Base-Emitter Saturation Voltage 基极发射极饱和压降(I _C = 500mA, I _B = 50mA) (I _C = 150mA, I _B = 15mA)	V _{BE(sat)}	—	—	1.2 0.95	V
Transition Frequency 特征频率(V _{CE} = 10V, I _C = 20mA)	f _T	250	—	—	MHz
Delay Time 延迟时间 (V _{CC} =30V, V _{BE} =-0.5V, I _C =150mA, I _{B1} =15mA)	t _d	—	—	10	ns
Rise Time 上升时间 (V _{CC} =30V, V _{BE} =-0.5V, I _C =150mA, I _{B1} =15mA)	t _r	—	—	25	ns
Storage Time 贮存时间 (V _{CC} =30V, I _C =150mA, I _{B1} =I _{B2} =15mA)	t _s	—	—	225	ns
Fall Time 下降时间 (V _{CC} =30V, I _C =150mA, I _{B1} =I _{B2} =15mA)	t _f	—	—	60	ns

■ Typical Characteristic Curve 典型特性曲线



■Dimension 外形封装尺寸



SOT-323 1.0

Symbol	Dimension in Millimeters	
	Min	Max
A	0.90	1.00
A1	0.010	0.100
B	1.20	1.40
bp	0.25	0.45
C	0.09	0.15
D	2.00	2.20
E	1.15	1.35
HE	2.15	2.55
Lp	0.25	0.46
θ	0°	6°